

# DATA SHEET

**PEMD4; PUMD4**  
NPN/PNP resistor-equipped  
transistors; R1 = 10 k $\Omega$ , R2 = open

Product specification  
Supersedes data of 2002 Jan 14

2003 Oct 10

**NPN/PNP resistor-equipped transistors;  
R1 = 10 kΩ, R2 = open**

**PEMD4; PUMD4**

**FEATURES**

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

**APPLICATIONS**

- Low current peripheral driver
- Replacement for general purpose transistors in digital applications
- Control of IC inputs.

**QUICK REFERENCE DATA**

| SYMBOL           | PARAMETER                 | TYP. | MAX. | UNIT |
|------------------|---------------------------|------|------|------|
| V <sub>CEO</sub> | collector-emitter voltage | –    | 50   | V    |
| I <sub>O</sub>   | output current (DC)       | –    | 100  | mA   |
| TR1              | NPN                       | –    | –    | –    |
| TR2              | PNP                       | –    | –    | –    |
| R1               | bias resistor             | 10   | –    | kΩ   |
| R2               | open                      | –    | –    | –    |

**DESCRIPTION**

NPN/PNP resistor-equipped transistors (see “Simplified outline, symbol and pinning” for package details).

**PRODUCT OVERVIEW**

| TYPE NUMBER | PACKAGE |       | MARKING CODE | PNP/PNP COMPLEMENT | NPN/PNP COMPLEMENT |
|-------------|---------|-------|--------------|--------------------|--------------------|
|             | PHILIPS | EIAJ  |              |                    |                    |
| PEMD4       | SOT666  |       | 23           | PEMB4              | PEMH4              |
| PUMD4       | SOT363  | SC-88 | D*4          | PUMB4              | PUMH4              |

**Note**

- \* = p: Made in Hong Kong.  
 \* = t: Made in Malaysia.  
 \* = W: Made in China.

**SIMPLIFIED OUTLINE, SYMBOL AND PINNING**

| TYPE NUMBER    | SIMPLIFIED OUTLINE AND SYMBOL | PINNING |               |
|----------------|-------------------------------|---------|---------------|
|                |                               | PIN     | DESCRIPTION   |
| PEMD4<br>PUMD4 | <p>Top view</p> <p>MDB814</p> | 1       | emitter TR1   |
|                |                               | 2       | base TR1      |
|                |                               | 3       | collector TR2 |
|                |                               | 4       | emitter TR2   |
|                |                               | 5       | base TR2      |
|                |                               | 6       | collector TR1 |

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#### ORDERING INFORMATION

| TYPE NUMBER | PACKAGE |  |         |
|-------------|---------|--|---------|
|             | NAME    | DESCRIPTION                              | VERSION |
| PEMD4       | –       | plastic surface mounted package; 6 leads | SOT666  |
| PUMD4       | –       | plastic surface mounted package; 6 leads | SOT363  |

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL   | PARAMETER                     | CONDITIONS               | MIN. | MAX. | UNIT |
|--|-------------------------------|--------------------------|------|------|------|
| <b>Per transistor; for the PNP transistor with negative polarity</b> |                               |                          |      |      |      |
| V <sub>CBO</sub>   | collector-base voltage        | open emitter             | –    | 50   | V    |
| V <sub>CEO</sub>   | collector-emitter voltage     | open base                | –    | 50   | V    |
| V <sub>EBO</sub>   | emitter-base voltage          | open collector           | –    | 5    | V    |
| I <sub>O</sub>   | output current (DC)           |                          | –    | 100  | mA   |
| I <sub>CM</sub>  | peak collector current        |                          | –    | 100  | mA   |
| P <sub>tot</sub>   | total power dissipation       | T <sub>amb</sub> ≤ 25 °C |      |      |      |
|  | SOT363                        | note 1                   | –    | 200  | mW   |
|  | SOT666                        | notes 1 and 2            | –    | 200  | mW   |
| T <sub>stg</sub>   | storage temperature           |                          | –65  | +150 | °C   |
| T <sub>j</sub>   | junction temperature          |                          | –    | 150  | °C   |
| T <sub>amb</sub>   | operating ambient temperature |                          | –65  | +150 | °C   |
| <b>Per device</b>  |                               |                          |      |      |      |
| P <sub>tot</sub>   | total power dissipation       | T <sub>amb</sub> ≤ 25 °C |      |      |      |
|  | SOT363                        | note 1                   | –    | 300  | mW   |
|  | SOT666                        | notes 1 and 2            | –    | 300  | mW   |

#### Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
2. Reflow soldering is the only recommended soldering method.

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**THERMAL CHARACTERISTICS**

| SYMBOL                | PARAMETER                                   | CONDITIONS               | VALUE | UNIT |
|-----------------------|---|--------------------------|-------|------|
| <b>Per transistor</b> |   |                          |       |      |
| R <sub>th j-a</sub>   | thermal resistance from junction to ambient | T <sub>amb</sub> ≤ 25 °C |       |      |
|                       | SOT363                                      | note 1                   | 625   | K/W  |
|                       | SOT666                                      | notes 1 and 2            | 625   | K/W  |
| <b>Per device</b>     |   |                          |       |      |
| R <sub>th j-a</sub>   | thermal resistance from junction to ambient | T <sub>amb</sub> ≤ 25 °C |       |      |
|                       | SOT363                                      | note 1                   | 416   | K/W  |
|                       | SOT666                                      | notes 1 and 2            | 416   | K/W  |

**Notes**

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
2. Reflow soldering is the only recommended soldering method.

**CHARACTERISTICS**

T<sub>amb</sub> = 25 °C unless otherwise specified.

| SYMBOL   | PARAMETER                            | CONDITIONS   | MIN. | TYP. | MAX. | UNIT       |
|--|--------------------------------------|--|------|------|------|------------|
| <b>Per transistor; for the PNP transistor with negative polarity</b> |                                      |  |      |      |      |            |
| I <sub>CBO</sub>   | collector-base cut-off current       | V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0                             | –    | –    | 100  | nA         |
| I <sub>CEO</sub>   | collector-emitter cut-off current    | V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0                             | –    | –    | 1    | $\mu$ A    |
|  |                                      | V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0; T <sub>j</sub> = 150 °C    | –    | –    | 50   | $\mu$ A    |
| I <sub>EBO</sub>   | emitter-base cut-off current         | V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0                              | –    | –    | 100  | nA         |
| h <sub>FE</sub>  | DC current gain                      | V <sub>CE</sub> = 5 V; I <sub>C</sub> = 1 mA                           | 200  | –    | –    |            |
| V <sub>CEsat</sub>   | collector-emitter saturation voltage | I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA                        | –    | –    | 150  | mV         |
| R1   | input resistor                       |  | 7    | 10   | 13   | k $\Omega$ |
| C <sub>c</sub>   | collector capacitance                | I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz |      |      |      |            |
|  | TR1 (NPN)                            |  | –    | –    | 2.5  | pF         |
|  | TR2 (PNP)                            |  | –    | –    | 3    | pF         |

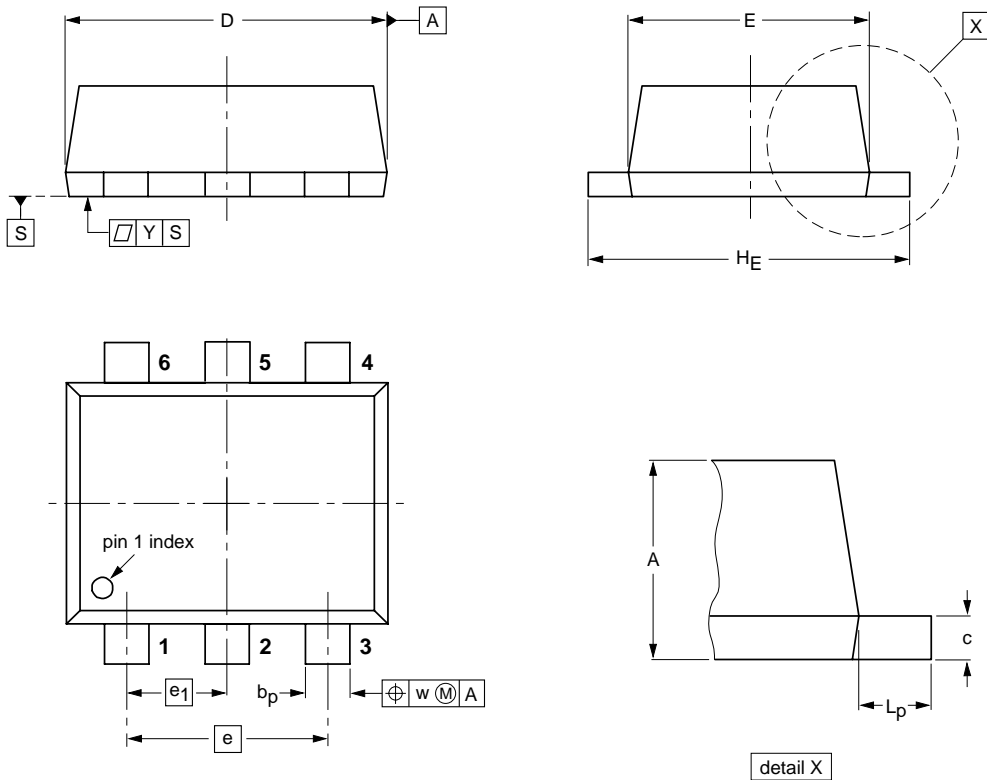
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PACKAGE OUTLINES

Plastic surface mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions)

| UNIT | A          | $b_p$        | c            | D          | E          | e   | $e_1$ | $H_E$      | $L_p$      | w   | y   |
|------|------------|--------------|--------------|------------|------------|-----|-------|------------|------------|-----|-----|
| mm   | 0.6<br>0.5 | 0.27<br>0.17 | 0.18<br>0.08 | 1.7<br>1.5 | 1.3<br>1.1 | 1.0 | 0.5   | 1.7<br>1.5 | 0.3<br>0.1 | 0.1 | 0.1 |

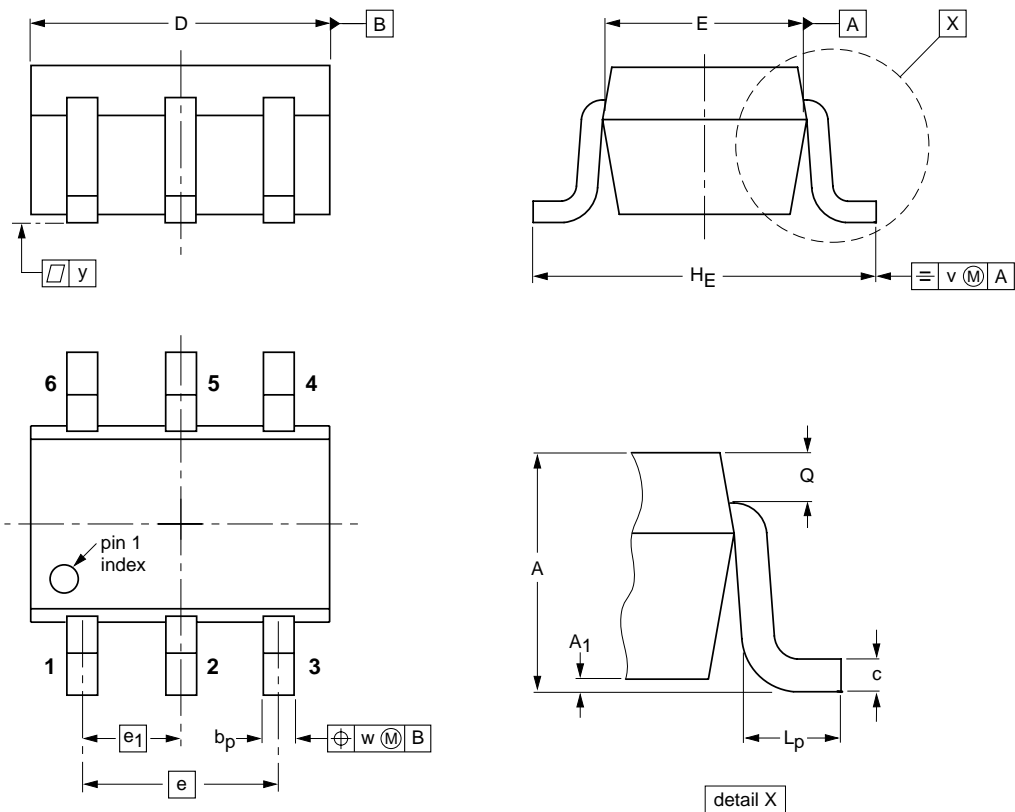
| OUTLINE VERSION | REFERENCES |       |      | EUROPEAN PROJECTION | ISSUE DATE           |
|-----------------|------------|-------|------|---------------------|----------------------|
|                 | IEC        | JEDEC | EIAJ |                     |                      |
| SOT666          |            |       |      |                     | 01-01-04<br>01-08-27 |

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SOT363



DIMENSIONS (mm are the original dimensions)

| UNIT | A          | A1<br>max | bp           | c            | D          | E            | e   | e1   | HE         | Lp           | Q            | v   | w   | y   |
|------|------------|-----------|--------------|--------------|------------|--------------|-----|------|------------|--------------|--------------|-----|-----|-----|
| mm   | 1.1<br>0.8 | 0.1       | 0.30<br>0.20 | 0.25<br>0.10 | 2.2<br>1.8 | 1.35<br>1.15 | 1.3 | 0.65 | 2.2<br>2.0 | 0.45<br>0.15 | 0.25<br>0.15 | 0.2 | 0.2 | 0.1 |

| OUTLINE<br>VERSION | REFERENCES |       |       |  | EUROPEAN<br>PROJECTION | ISSUE DATE |
|--------------------|------------|-------|-------|--|------------------------|------------|
|                    | IEC        | JEDEC | EIAJ  |  |                        |            |
| SOT363             |            |       | SC-88 |  |                        | 97-02-28   |

NPN/PNP resistor-equipped transistors;  
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#### DATA SHEET STATUS

| LEVEL | DATA SHEET STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)(3)</sup> | DEFINITION   |
|-------|----------------------------------|----------------------------------|--|
| I     | Objective data                   | Development                      | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.  |
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**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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